

Super Barrier Rectifier ™

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

Characteristics	Values	Units
I _{F(AV)} Rectangular Waveform	60	Α
V_{RRM}	60	V
V _F @30A, Tj=125 ^O C	0.58	V, typ
Tj (operating/storage)	-65 to 150	°C

ELECTRICAL:

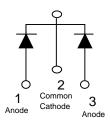
- * Low Forward Voltage Drop
- * Reliable High Temperature Operation
- * Super Barrier Design
- * Softest, fast switching capability
- * 150°C Operating Junction Temperature

Device optimized for low forward voltage drop to maximize efficiency in Power Supply applications

MECHANICAL:

* Molded Plastic TO-220 package





Maximum Ratings and Electrical Characteristics (at 25°C unless otherwise specified)						
20	SYMBOL			UNITS		
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	$egin{array}{c} egin{array}{c} egin{array}{c} V_{RM} \ egin{array}{c} V_{RRM} \end{array}$	6	60			
Average Rectified Forward Current (Rated V _R -20Khz Square Wave) - 50% duty cycle	I _o	60		Amps		
Peak Forward Surge Current - 1/2 60hz	I _{FSM}	350		Amps		
Peak Repetitive Reverse Surge Current (2uS-1Khz)	I _{RRM}	3		Amps		
Instantaneous Forward Voltage (per leg) $I_F = 30A$; $T_J = 25^{\circ}C$ $I_F = 30A$; $T_J = 125^{\circ}C$	V _F *	Typ 	Max 0.73 0.63	Volts		
Maximum Instantaneous Reverse Current at Rated V_{RM} $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I _R	Typ 	Max 0.5 100	mA mA		
Maximum Rate of Voltage Change (at Rated V _R)	dv/dt	10,000		V/uS		
Maximum Thermal Resistance JC (per leg)	R⊕ _{JC}	2		°C/W		
Operating and Storage Junction Temperature	TJ	-65 to +150		°C		

^{*} Pulse width < 300 uS, Duty cycle < 2%

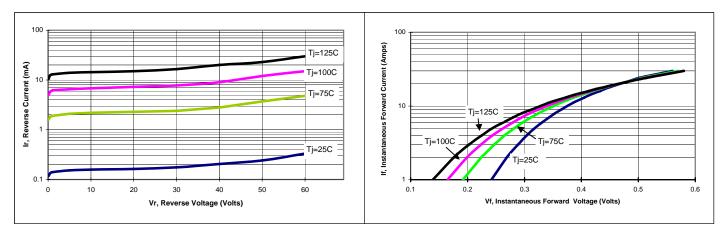


Figure 1: Typical Reverse Current (per leg)

Figure 2: Typical Forward Voltage (per leg)

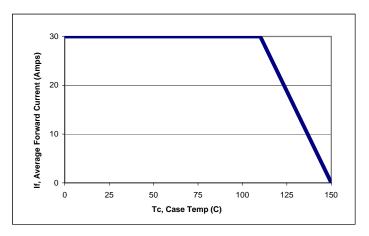


Figure 3: Current Derating, Case (per leg)

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